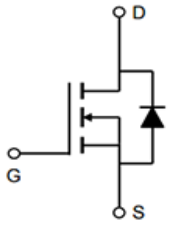
EFMICRO
Semiconductor Limited Company

BSS123

N-Channel Advanced Power MOSFET

• Product Summary

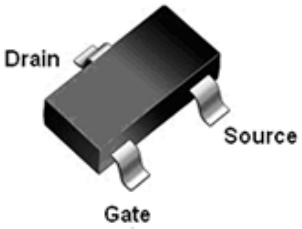
Part #	V_{DS}	$R_{DS(on).typ}$ ($@V_{GS}$=10V)	$R_{DS(on).typ}$ ($@V_{GS}$=4.5V)	I_D
BSS123	100V	3.5Ω	3.8Ω	0.17A



N-Channel MOSFET

• Features

- Surface Mount Package
- High Density Cell Design for Extremely Low $R_{DS(ON)}$
- Voltage Controlled Small Signal Switch
- Rugged and Reliable



SOT-23

RoHS

HF

•Application

- Small Servo Motor Controls
- Power MOSFET Gate Drivers
- Switching Application

•Ordering Information:

Part NO.	BSS123
Marking	SA
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

•Absolute Maximum Ratings (T_C=25℃)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	0.17	A
Drain Current-Pulsed (Note 1)	I_{DM}	0.7	A
Maximum Power Dissipation	P_D	0.35	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

•Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	357	℃/W

● Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250uA	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=100VV_{GS}=0V	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V V_{DS}=0V	--	--	±50	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} I_D=250uA	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V I_D=0.17A	--	3.5	3.9	Ω
		V_{GS}=4.5V I_D=0.17A	--	3.8	5	Ω
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=25V V_{GS}=0V F=1.0MHz	--	29	--	PF
Output Capacitance	C_{oss}		--	10	--	PF
Reverse Transfer Capacitance	C_{rss}		--	2	--	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=30V I_D=0.28A V_{GS}=10V R_G=50Ω,	--	8	--	nS
Turn-on Rise Time	t_r		--	8	--	nS
Turn-Off Delay Time	$t_{d(off)}$		--	13	--	nS
Turn-Off Fall Time	t_f		--	16	--	nS
Total Gate Charge	Q_g	V_{DS}=25V I_D=0.22A V_{GS}=10V	--	1.4	--	nC
Gate-Source Charge	Q_{gs}		--	0.15	--	nC
Gate-Drain Charge	Q_{gd}		--	0.2	--	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V I_S=0.17A	--	0.79	1.2	V
Diode Forward Current (Note 2)	I_S		--	--	0.17	A

Notes :

1.Surface mounted on FR4 board using the minimum recommended pad size.

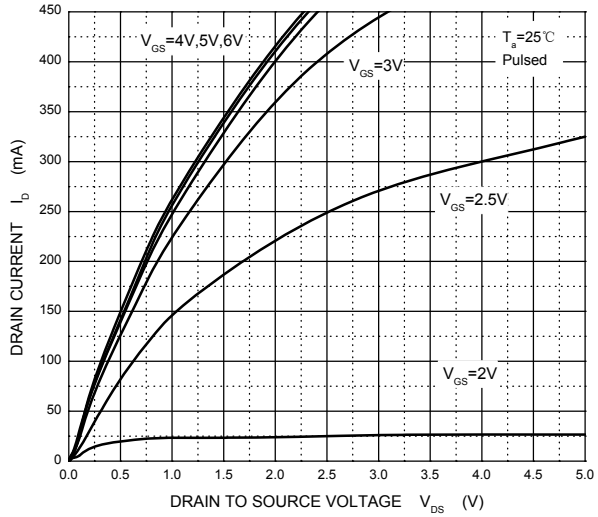
2. Pulse Test : Pulse width=300μs, duty cycle≤2%.

3. Switching characteristics are independent of operating junction temperature.

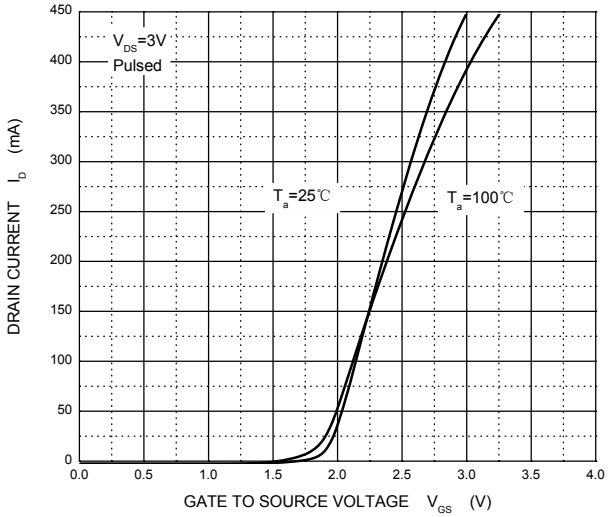
4. Graranted by design，not subject to producting.

• Typical Characteristics

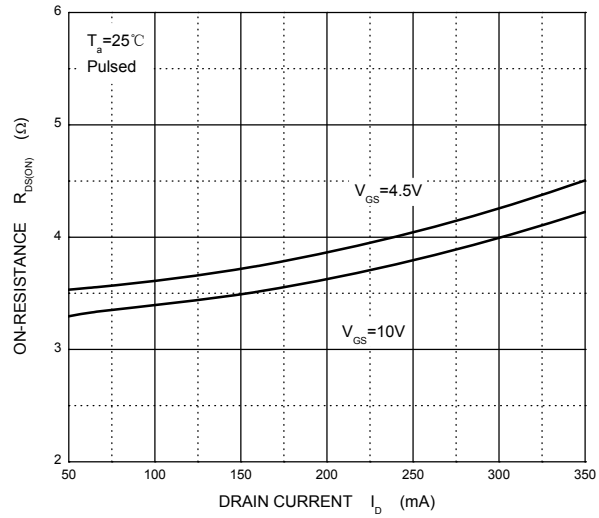
Output Characteristics



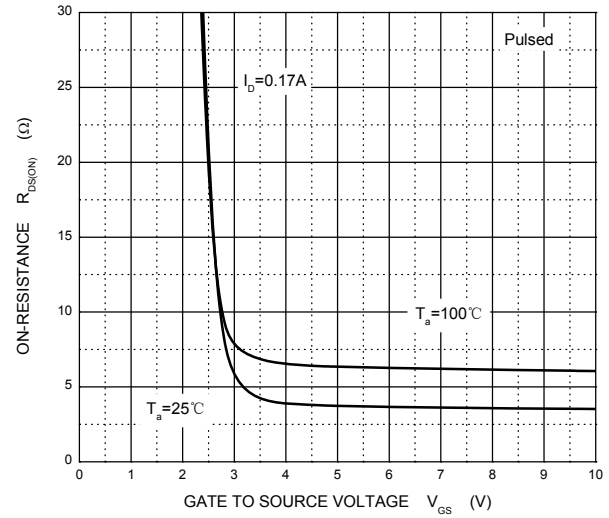
Transfer Characteristics



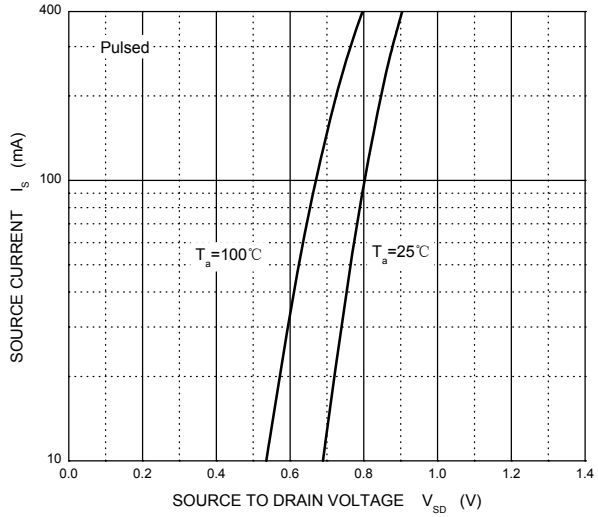
$R_{DS(ON)}$ —— I_D



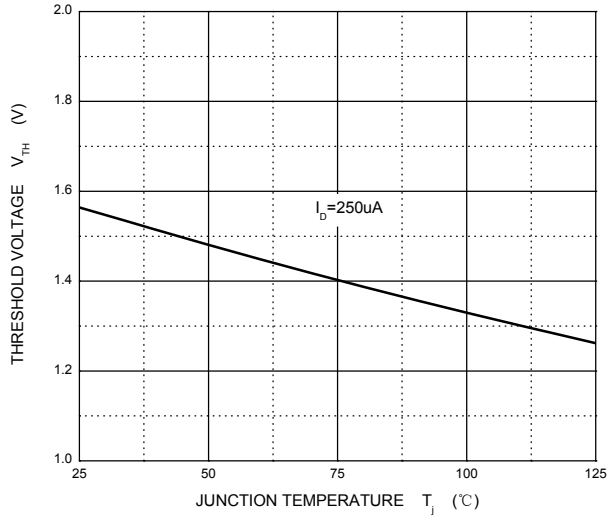
$R_{DS(ON)}$ —— V_{GS}



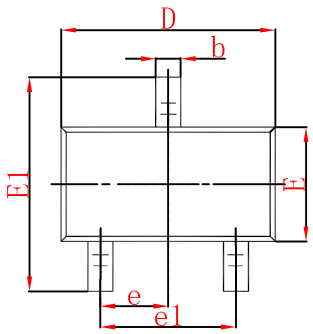
I_S —— V_{SD}

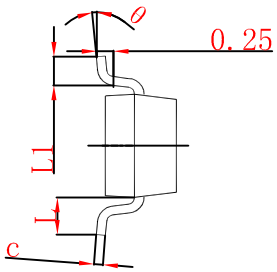


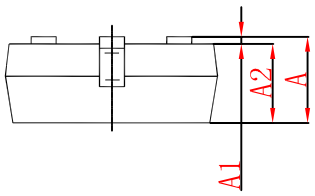
Threshold Voltage



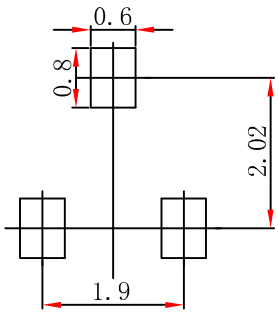
SOT-23 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.